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PMSTA3904

40 V, 200 mA NPN switching transistor

Rev. 01 — 21 April 2008

Product data sheet

1. Product profile

1.1 General description

Single NPN switching transistor in a SOT323 (SC-70) very small Surface-Mounted Device (SMD) plastic package.

PNP complement: PMST3906.

1.2 Features

- Single NPN switching transistor
- Integrated extraction electrode for fast switching
- AEC-Q101 qualified

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	40	V
I _C	collector current		-	-	200	mA
h _{FE}	DC current gain	$V_{CE} = 1 V;$ $I_{C} = 10 \text{ mA}$	100	195	300	

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base		_
2	emitter	3	3
3	collector		1——
		1 2	2
			006aab209



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3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PMSTA3904	SC-70	plastic surface-mounted package; 3 leads	SOT323	

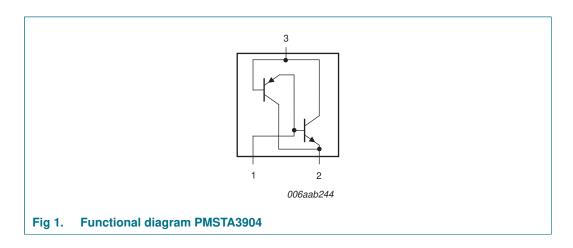
4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMSTA3904	*1Y

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Functional diagram



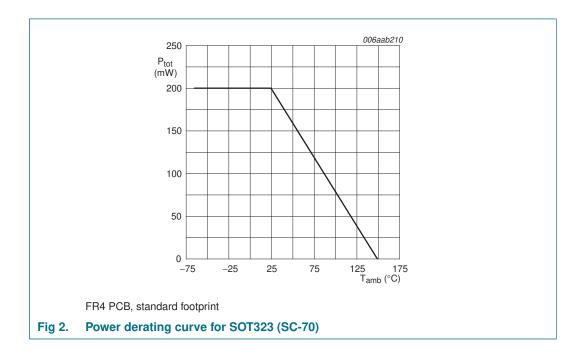
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6. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

		• •	•		
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	60	V
V_{CEO}	collector-emitter voltage	open base	-	40	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	200	mA
I _{CR}	reverse collector current	open base	-	20	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



PMSTA3904 NXP Semiconductors

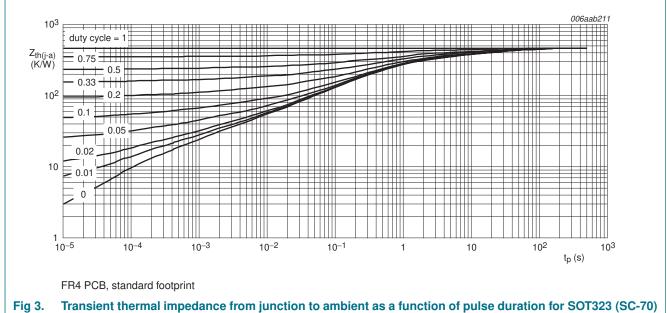
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Thermal characteristics

Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	625	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	175	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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8. Characteristics

Table 7. Characteristics

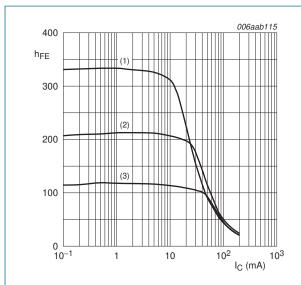
 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$	-	-	50	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; I_{C} = 0 \text{ A}$	-	-	50	nA
h _{FE}	DC current gain	V _{CE} = 1 V				
		$I_C = 0.1 \text{ mA}$	60	195	-	
		$I_C = 1 \text{ mA}$	80	195	-	
		$I_C = 10 \text{ mA}$	100	195	300	
		$I_C = 50 \text{ mA}$	60	105	-	
		$I_C = 100 \text{ mA}$	30	50	-	
V _{CEsat}	collector-emitter	$I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$	-	75	200	mV
	saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	-	120	300	mV
V _{ECO}	emitter-collector voltage	$I_{CR} = 1 \text{ mA}; I_{B} = 0 \text{ A}$	-	660	-	mV
V _{BEsat} base-emitter satu voltage	base-emitter saturation	$I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$	650	750	850	mV
	voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	-	850	950	mV
f _T	transition frequency	$V_{CE} = 20 \text{ V};$ $I_{C} = 10 \text{ mA};$ $f = 100 \text{ MHz}$	300	-	-	MHz
C _c	collector capacitance	$V_{CB} = 5 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	4	pF
C _e	emitter capacitance	$V_{BE} = 0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	8	pF
NF	noise figure	$V_{CE} = 5 \text{ V};$ $I_{C} = 100 \mu\text{A};$ $R_{S} = 1 k\Omega;$ $f = 10 \text{Hz}$ to 15.7 kHz	-	-	5	dB
t _d	delay time	$V_{CC} = 3 V;$	-	-	35	ns
t _r	rise time	$I_C = 10 \text{ mA};$	-	-	35	ns
t _{on}	turn-on time	$-I_{Bon} = 1 \text{ mA};$ $I_{Boff} = -1 \text{ mA}$	-	-	70	ns
t _s	storage time		-	-	200	ns
t _f	fall time	_	-	-	50	ns
t _{off}	turn-off time		_	_	250	ns

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10³

I_C (mA)



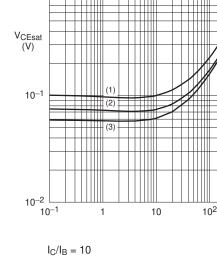
$$V_{CE} = 1 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 4. DC current gain as a function of collector current; typical values



(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values

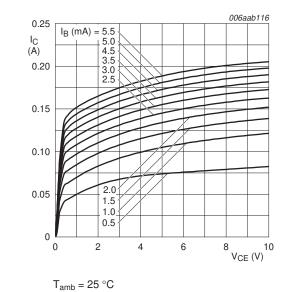
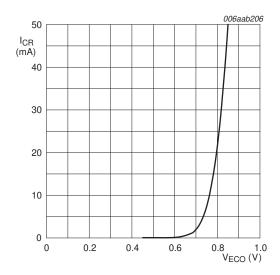


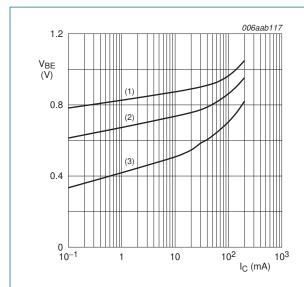
Fig 6. Collector current as a function of collector-emitter voltage; typical values



 $I_B = 0 A; T_{amb} = 25 °C$

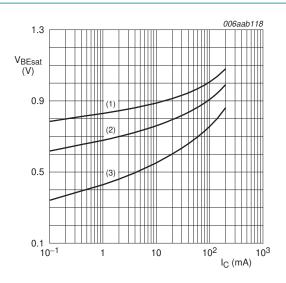
Fig 7. Reverse collector current as a function of emitter-collector voltage; typical values

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- $V_{CE} = 1 V$
- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

Fig 8. Base-emitter voltage as a function of collector current; typical values



- $I_{\rm C}/I_{\rm B} = 10$
- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

Fig 9. Base-emitter saturation voltage as a function of collector current; typical values

9. Test information

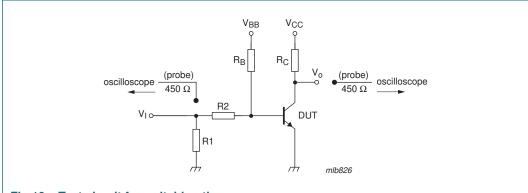


Fig 10. Test circuit for switching times

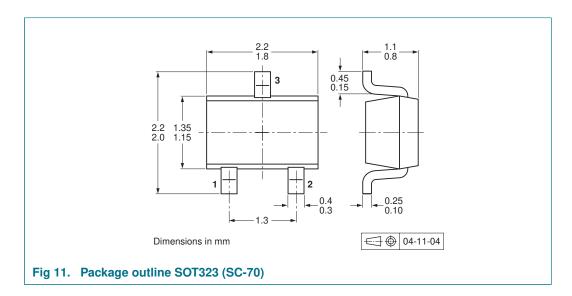
9.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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10. Package outline



11. Packing information

Table 8. Packing methods

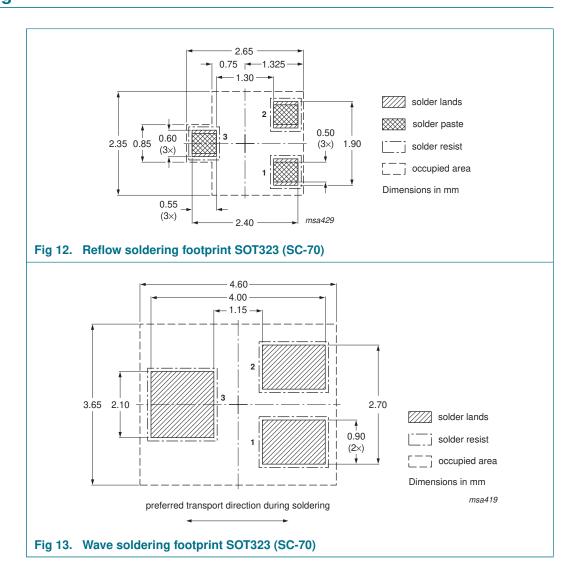
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMSTA3904	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135

^[1] For further information and the availability of packing methods, see Section 15.

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12. Soldering



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13. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMSTA3904_1	20080421	Product data sheet	-	-

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14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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